

DZ36082D0L

Silicon epitaxial planar type

For surge absorption circuit

■ Features

- Excellent rising characteristics of zener current I_Z
- Low zener operating resistance R_Z
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 03

■ Packaging

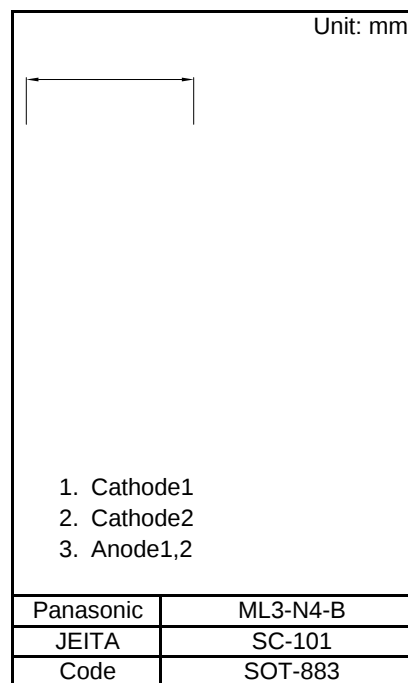
Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Rating	Unit
Total power dissipation ^{*1}	PT	200	mW
Electrostatic discharge ^{*2}	ESD	±10	kV
Junction temperature	T_j	150	$^{\circ}\text{C}$
Operating ambient temperature	T_{opr}	-40 to +85	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Note) *1: PT = 200 mW achieved with a printed circuit board.
(2 Diode total)

*2: Test method:IEC61000_4_2($C = 150\text{ pF}$, $R = 330\text{ }\Omega$, Contact discharge:10 times)



Internal Connection

■ Electrical Characteristics $T_a = 25\text{ }^{\circ}\text{C} \pm 3\text{ }^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	$I_F = 10\text{ mA}$			1.0	V
Zener voltage ^{*1, *2}	VZ	$I_Z = 5\text{ mA}$	7.79		8.61	V
Zener operating resistance	RZ	$I_Z = 5\text{ mA}$			30	Ω
Zener rise operating resistance	RZK	$I_Z = 0.5\text{ mA}$			60	Ω
Reverse current	IR	$V_R = 5\text{ V}$			0.1	μA
Temperature coefficient of zener voltage ^{*3}	SZ	$I_Z = 5\text{ mA}$		4.8		mV/ $^{\circ}\text{C}$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. *1: The temperature must be controlled 25°C for VZ measurement.

VZ value measured at other temperature must be adjusted to VZ (25°C)

*2: VZ guaranteed 20 ms after current flow.

*3: $T_j = 25^{\circ}\text{C}$ to 150°C